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Supporting Information

Low-Voltage Solution-Processed Graphene Transistors Based on Chemically and Solvothermally Reduced Graphene Oxide

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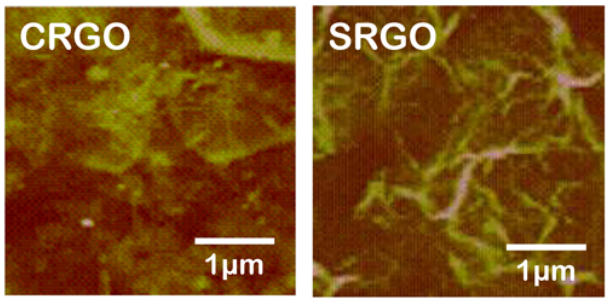

Figure S1. AFM images of chemically- and solvothermally-reduced graphene oxide films.

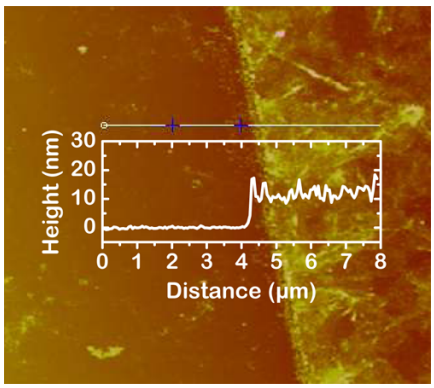

Figure S2. AFM image and its corresponding height profile of chemically-reduced graphene oxide film.

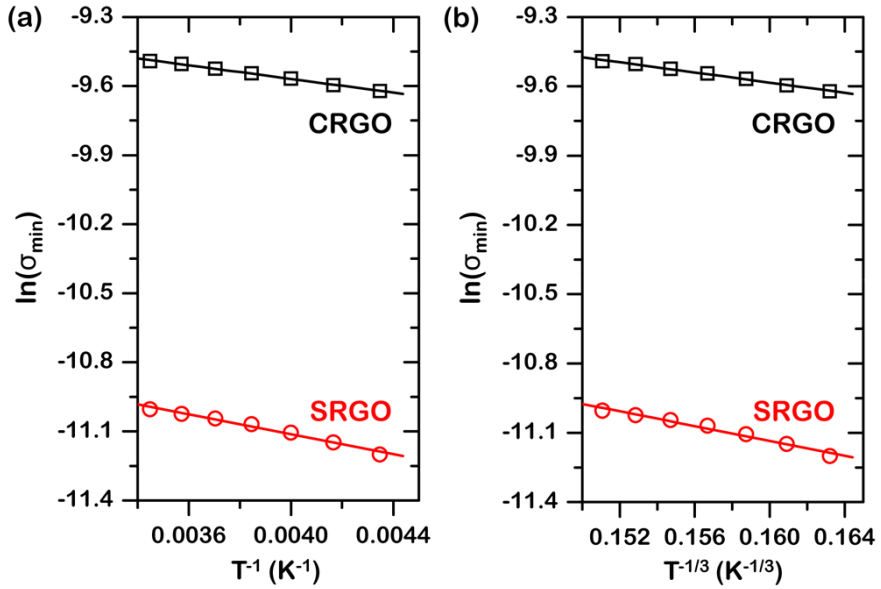

Figure S3. (a) $ln(\sigma_{min})$ *vs.* T^{-1} plots (b) $ln(\sigma_{min})$ *vs.* $T^{-1/3}$ plots of ion gel-gated graphene FETs based on chemically- and solvothermally-reduced graphene oxides.

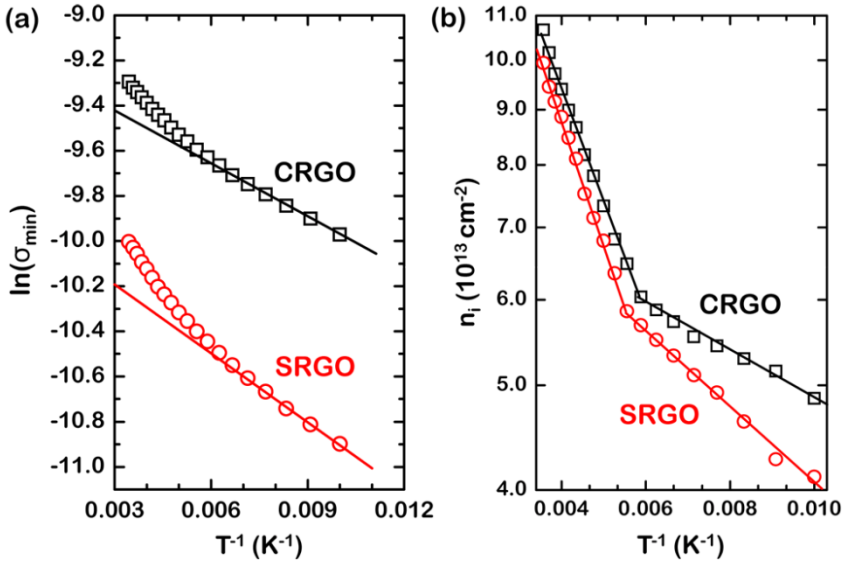

Figure S4. (a) $ln(\sigma_{min})$ *vs.* T^{-1} plots and (b) n_i *vs.* T^{-1} plots of SiO_2-gated graphene FETs based on chemically- and solvothermally-reduced graphene oxides.